



(use as many sheets as necessary)

Sheet	1	of	2
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Attorney Docket Number	018865-003600US
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known			
		Application Number	09/448,884		
		Filing Date	November 24, 1999		
		First Named Inventor	Sharp, Joelle		
		Art Unit	2818		
		Examiner Name	David Vu		
Sheet	2	of	2	Attorney Docket Number	018865-003600US

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DV	0005	CHANG et al., "A Highly Manufacturable Corner Rounding Solution for 0.18 μ m Shallow Trench Isolation," IEDM Tech. Digest, pp. 661-664 (1997).	
	0006	NOURI et al., "An Optimized Shallow Trench Isolation for sub-0.18 μ m ASIC Technologies," SPIE Vol. 3506, pp. 156- 166 (September 1998).	
	0007	MATSUDA et al., "Novel Corner Rounding Process for Shallow Trench Isolation utilizing MSTs (Micro-Structure Transformation of Silicon)," IEDM Tech. Digest, pp. 137-140 (December 1998).	
DV	0008	NANDAKUMAR et al., "Shallow Trench Isolation for advanced ULSI CMOS Technologies," IEDM Tech. Digest, pp. 133-136 (December 1998).	

Examiner Signature	<i>gheland</i>	Date Considered	07/19/04
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Application Number	09/448,884
Filing Date	November 24, 1999
First Named Inventor	Joelle Sharp, et al.
Group Art Unit	2811
Examiner Name	Unassigned
Attorney Docket Number	018865003600

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

[illegible]

**Examiner
Signature**

Hubbard

Date Considered

08/03/04.

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